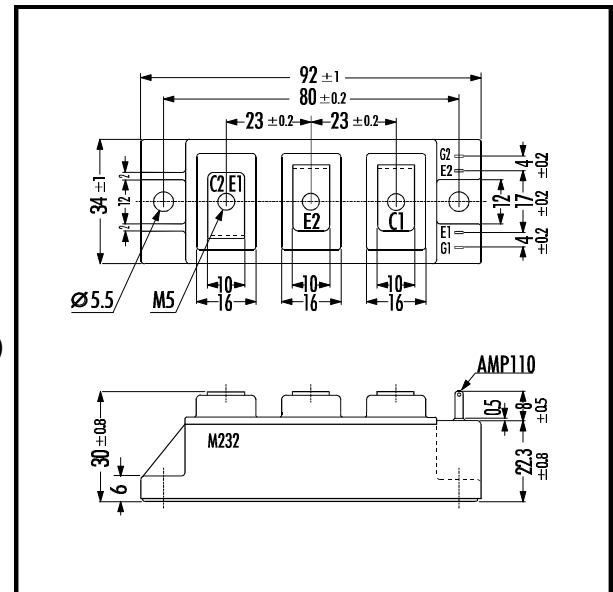


IGBT MODULE (N series)

■ Outline Drawing

■ Features

- Square RBSOA
- Low Saturation Voltage
- Overcurrent Limiting Function (~3 Times Rated Current)



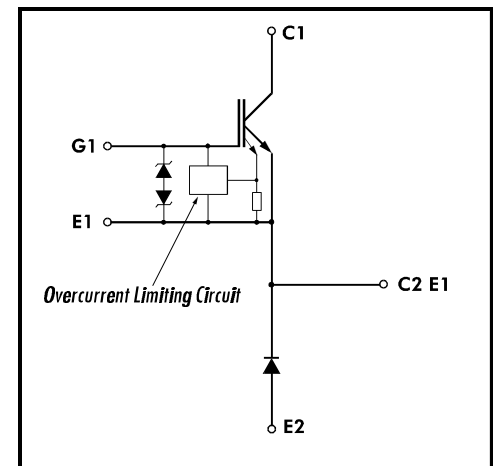
■ Maximum Ratings and Characteristics

• Absolute Maximum Ratings (T_c=25°C)

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V _{CES}	600	V
Gate -Emitter Voltage	V _{GES}	± 20	V
Collector Current	Continuous	I _C	200
	1ms	I _{C PULSE}	400
	Continuous	-I _C	200
	1ms	-I _{C PULSE}	400
Max. Power Dissipation	P _C	780	W
Operating Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Isolation Voltage	A.C. 1min.	V _{is}	2500
Screw Torque	Mounting *1	3.5	Nm
	Terminals *1	3.5	

Note: *1:Recommendable Value; 2.5 ~ 3.5 Nm (M5)

■ Equivalent Circuit



• Electrical Characteristics (at T_j=25°C)

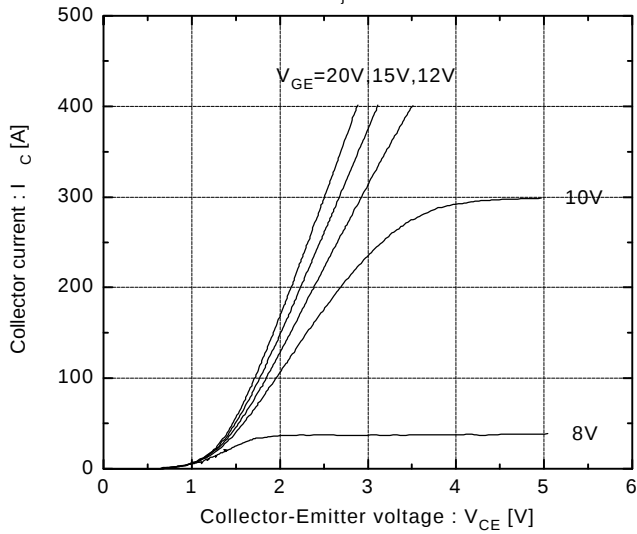
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I _{CES}	V _{GE} =0V V _{CE} =600V			2.0	mA
Gate-Emitter Leakage Current	I _{GES}	V _{CE} =0V V _{GE} =± 20V			30	μA
Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{GE} =20V I _C =200mA	4.5		7.5	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V I _C =200A			2.8	V
Input capacitance	C _{ies}	V _{GE} =0V		13200		pF
Output capacitance	C _{oes}	V _{CE} =10V		2930		
Reverse Transfer capacitance	C _{res}	f=1MHz		1330		
Turn-on Time	t _{ON}	V _{CC} =300V		0.6	1.2	μs
Turn-off Time	t _r	I _C =200A		0.2	0.6	
	t _{OFF}	V _{GE} =± 15V		0.6	1.0	
	t _f	R _G =9.1Ω		0.2	0.35	
Diode Forward On-Voltage	V _F	I _F =200A V _{GE} =0V			3.0	V
Reverse Recovery Time	t _{rr}	I _F =200A			300	ns
Reverse Current	I _{RRM}	V _R =600V			2.0	mA

• Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R _{th(j-c)}	IGBT			0.16	°C/W
	R _{th(j-e)}	Diode			0.35	
	R _{th(c-f)}	With Thermal Compound		0.025		

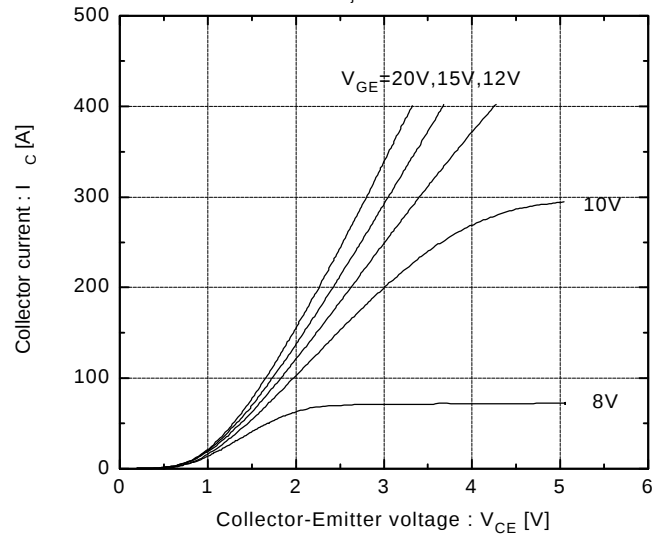
Collector current vs. Collector-Emittor voltage

$T_J = 25^\circ\text{C}$



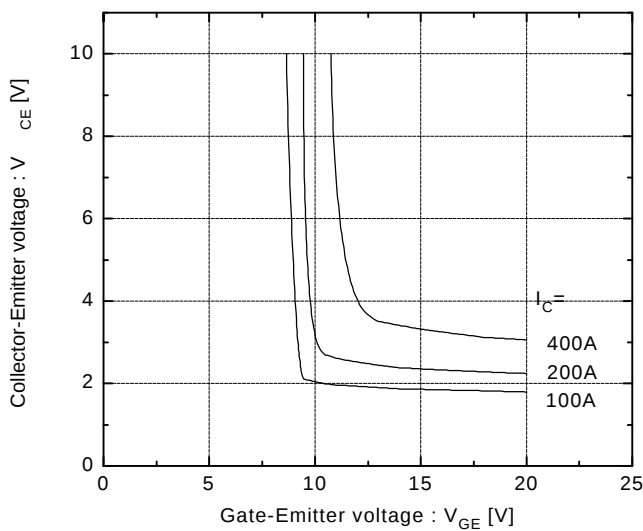
Collector current vs. Collector-Emittor voltage

$T_J = 125^\circ\text{C}$



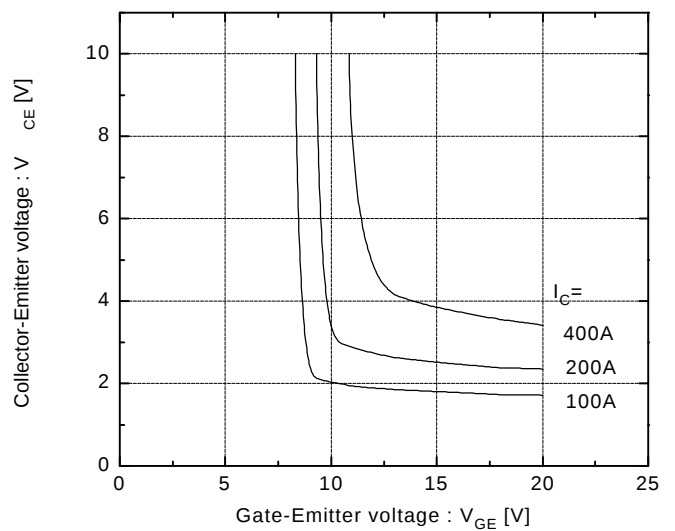
Collector-Emittor vs. Gate-Emittor voltage

$T_J = 25^\circ\text{C}$



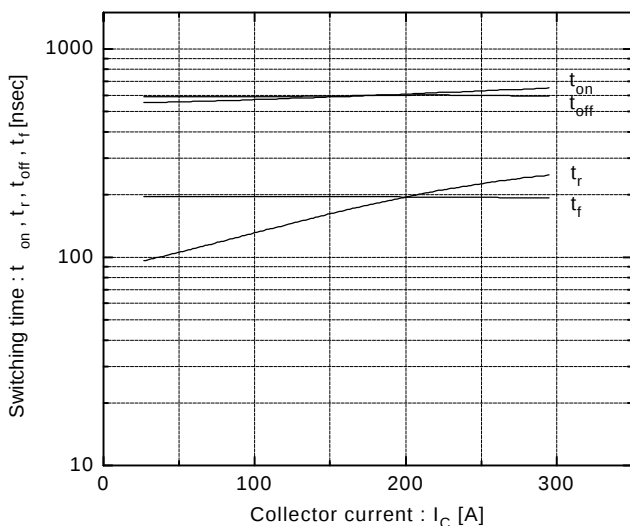
Collector-Emittor vs. Gate-Emittor voltage

$T_J = 125^\circ\text{C}$



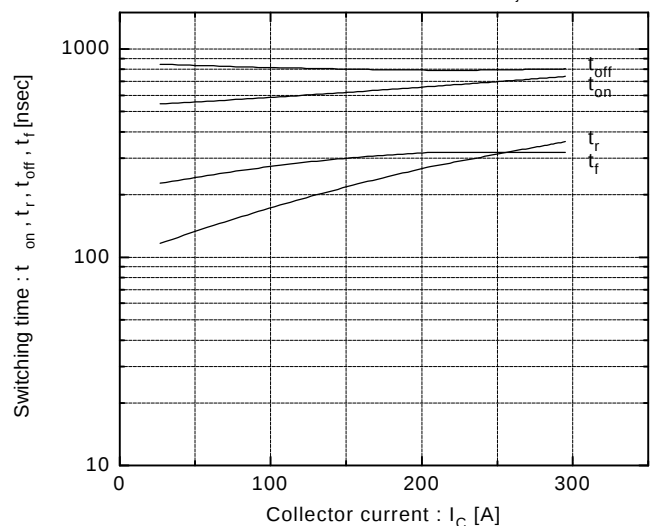
Switching time vs. Collector current

$V_{CC} = 300\text{V}$, $R_G = 9.1\Omega$, $V_{GE} = \pm 15\text{V}$, $T_J = 25^\circ\text{C}$



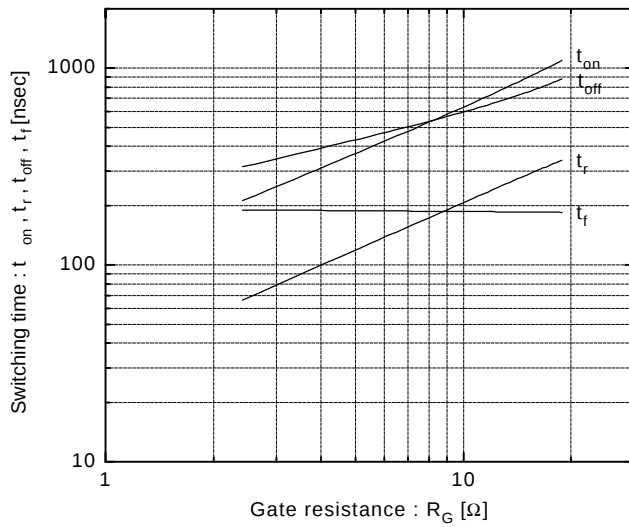
Switching time vs. Collector current

$V_{CC} = 300\text{V}$, $R_G = 9.1\Omega$, $V_{GE} = \pm 15\text{V}$, $T_J = 125^\circ\text{C}$



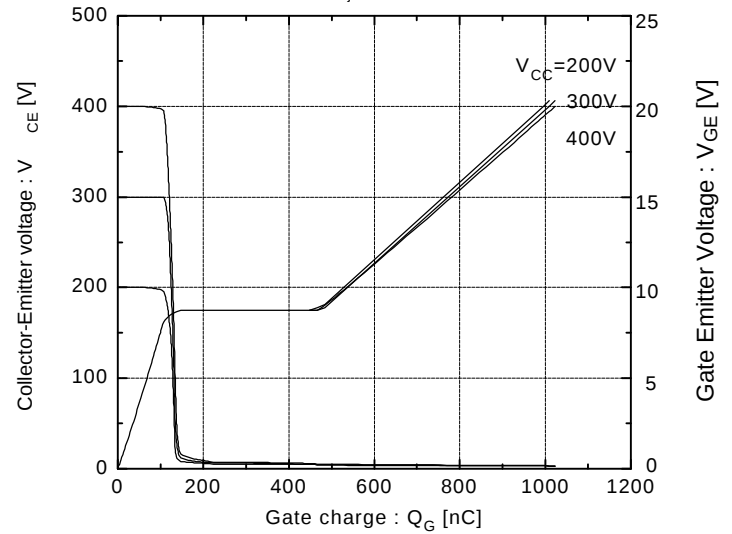
Switching time vs. R_G

$V_{CC}=300V$, $I_C=200A$, $V_{GE}=\pm 15V$, $T_J=25^\circ C$



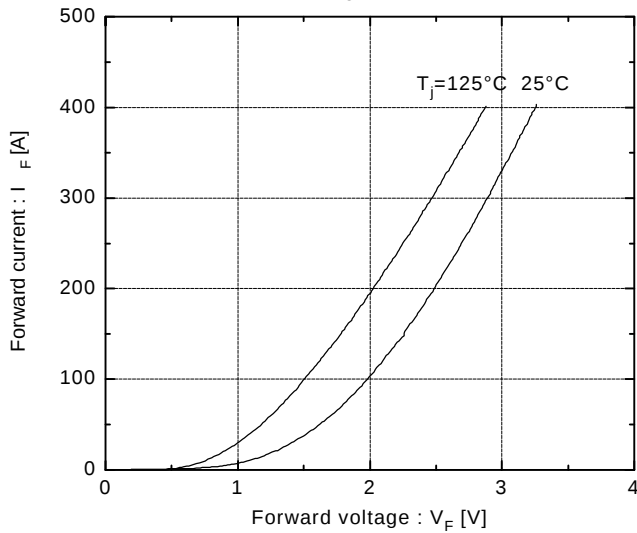
Dynamic input characteristics

$T_J=25^\circ C$



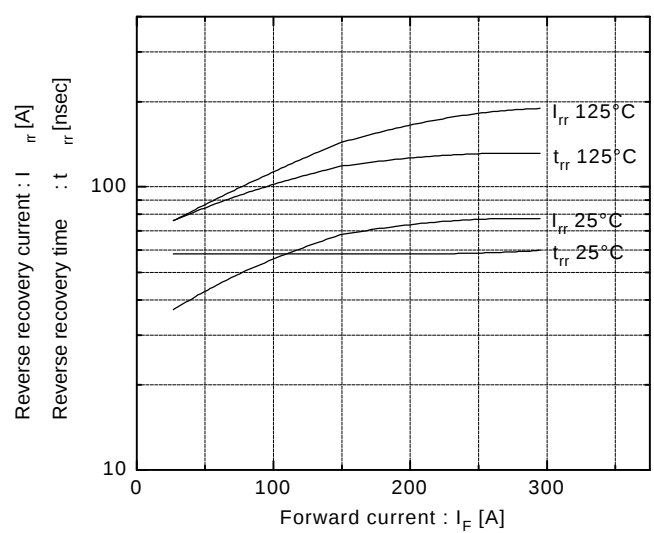
Forward current vs. Forward voltage

$V_{GE}=0V$

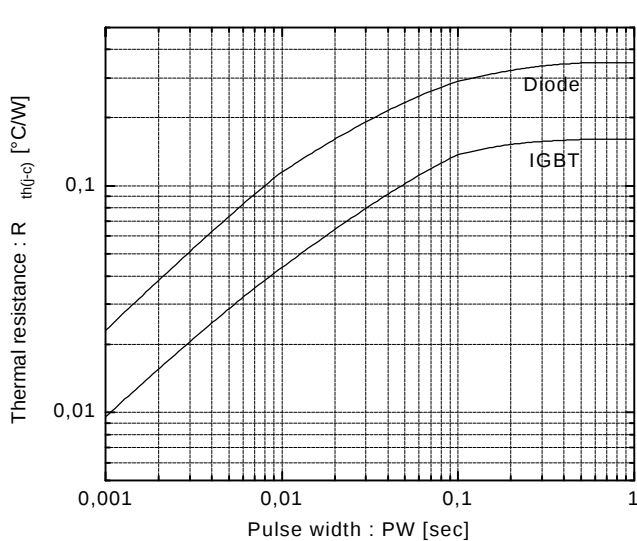


Reverse recovery characteristics

t_{rr} , I_{rr} vs. I_F

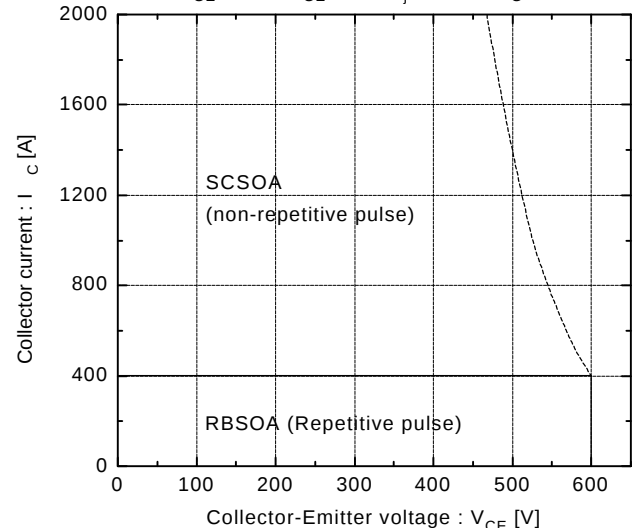


Transient thermal resistance

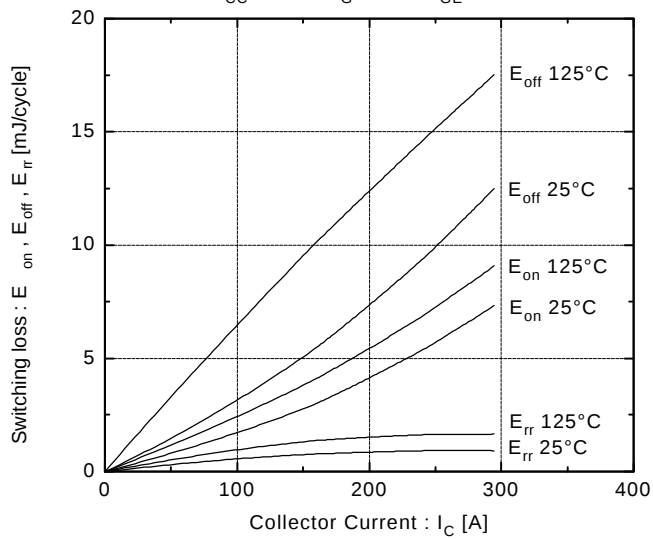


Reversed biased safe operating area

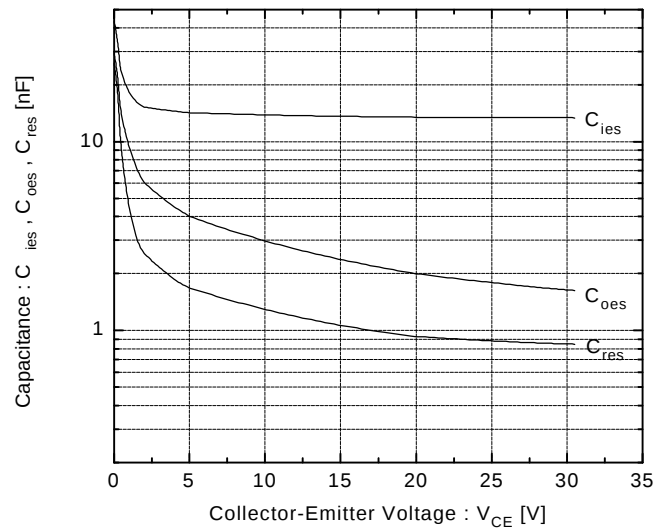
$+V_{GE}=15V$, $-V_{GE}\leq 15V$, $T_J\leq 125^\circ C$, $R_G\geq 9.1\Omega$



Switching loss vs. Collector current
 $V_{CC}=300V$, $R_G=9.1\Omega$, $V_{GE}=\pm 15V$



Capacitance vs. Collector-Emitter voltage
 $T_J=25^\circ C$



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